Silicon NPN Power Transistors 2SC3025

DESCRIPTION

·With TO-3 package
·High breakdown voltage

APPLICATIONS

·High voltage power switching character display horizontal deflection output

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

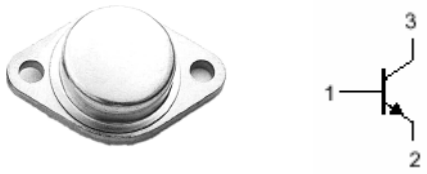

Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T_a=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CP}	Collector current-peak		6	A
P_C	Collector power dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-45~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ;R_{BE}=∞	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=10mA; I_C=0	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=5A; I_B=1.25A			2.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=5A; I_B=1.25A			1.5	V
I_{CES}	Collector cut-off current	V_{CE}=1500V; R_{BE}=∞			0.5	mA
Switching times						
t_s	Storage time	I_C=5A; I_{B1}=1A;I_{B2}=-2.5A		4.0		μs
t_f	Fall time				0.5	μs

PACKAGE OUTLINE

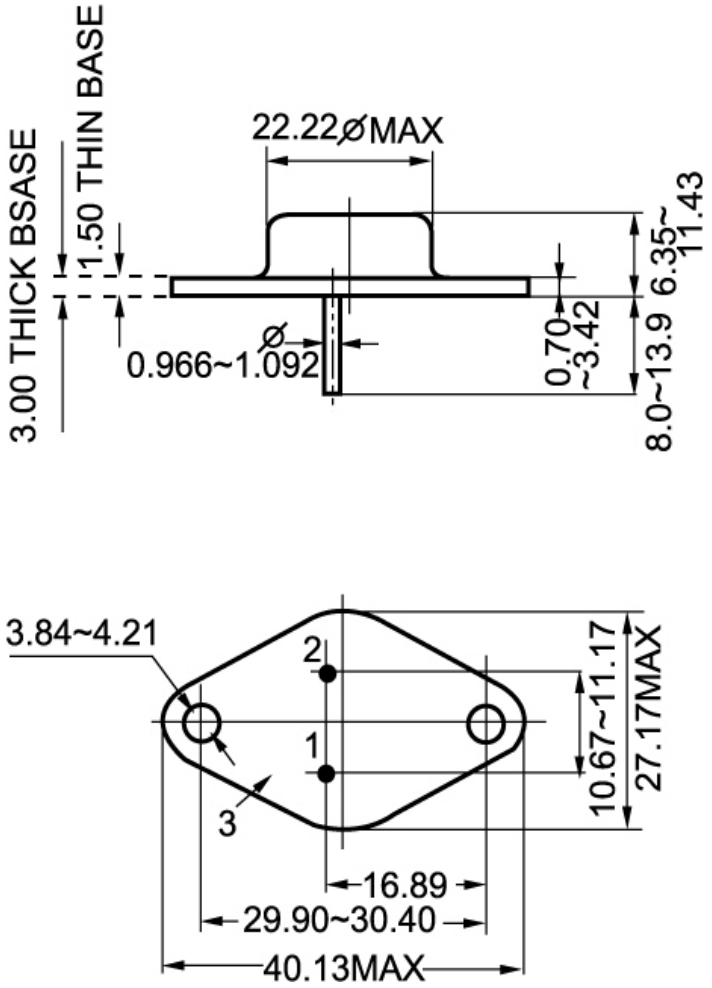

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)